

ABSTRACT OF THE DISCLOSURE

- Slurries for use in the chemical mechanical polishing (CMP) of copper and copper diffusion barriers that reduce pattern sensitive erosion of an underlying dielectric layer include at least one surfactant. Inclusion of surfactants, such as
- 5 cetyltrimethylammonium bromide in a slurry mixture can reduce pattern sensitive erosion of dielectric materials such as silicon oxide, and fluorinated oxides of silicon that would otherwise occur during CMP of copper and copper diffusion barriers as is typical in the formation of copper interconnect lines in integrated circuits.

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